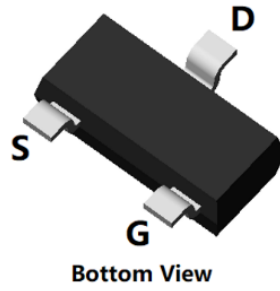
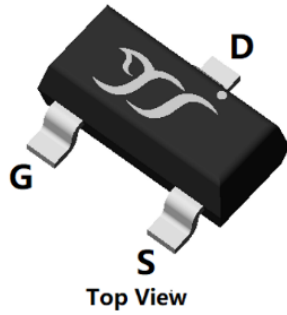
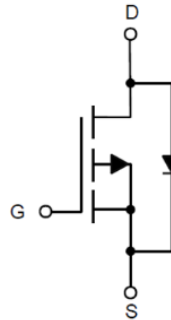


P-Channel Enhancement Mode Field Effect Transistor



SOT-23



Product Summary

• V_{DS}	-30V
• I_D	-4.1A
• $R_{DS(ON)}$ (at $V_{GS}=-10V$)	<49mohm
• $R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	<65mohm

General Description

- Trench Power LV MOSFET technology
- High density cell design for Low $R_{DS(ON)}$
- High Speed switching
- Part no. with suffix "Q" means AEC-Q101 qualified

Applications

- Battery protection
- Load switch
- Power management

■ Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-source Voltage	V_{DS}	-30	V
Gate-source Voltage	V_{GS}	± 20	V
Drain Current	I_D	$T_A=25^{\circ}C$	-4.1
		$T_A=70^{\circ}C$	-3.2
Pulsed Drain Current ^A	I_{DM}	-15	A
Total Power Dissipation	P_D	$T_A=25^{\circ}C$	1.2
		$T_A=70^{\circ}C$	0.8
Thermal Resistance Junction-to-Ambient ^B	$R_{\theta JA}$	105	$^{\circ}C/W$
Junction and Storage Temperature Range	T_J, T_{STG}	-55~+150	$^{\circ}C$

■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL3407AQ	F2	3407.	3000	30000	120000	7" reel



YJL3407AQ

■ Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-30			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V, T_J=25^\circ\text{C}$			-1	μA
		$V_{DS}=-30V, V_{GS}=0V, T_J=150^\circ\text{C}$		-5		μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 10V, V_{DS}=0V$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1	-1.5	-2.4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-4.1A$		36	49	m Ω
		$V_{GS}=-4.5V, I_D=-3.5A$		52	65	
Diode Forward Voltage	V_{SD}	$I_S=-4.1A, V_{GS}=0V$			-1.2	V
Dynamic Parameters						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$		572		pF
Output Capacitance	C_{oss}			82		
Reverse Transfer Capacitance	C_{rss}			70		
Switching Parameters						
Total Gate Charge	Q_g	$V_{GS}=-10V, V_{DS}=-15V, I_D=-4.1A$		11.65		nC
Gate-Source Charge	Q_{gs}			2.32		
Gate-Drain Charge	Q_{gd}			2.08		
Reverse Recovery Charge	Q_{rr}	$I_F=-10A, di/dt=100A/\mu s$		0.643		nC
Reverse Recovery Time	t_{rr}			15.7		
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=-10V, V_{DS}=-15V, R_L=15\Omega$ $R_{GEN}=2.5\Omega$		3.8		ns
Turn-on Rise Time	t_r			17.6		
Turn-off Delay Time	$t_{D(off)}$			17.8		
Turn-off fall Time	t_f			21.8		

A. Pulse Test: Pulse Width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

B. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design, while $R_{\theta JA}$ is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² FR-4 board with 2oz copper.



■ Typical Performance Characteristics

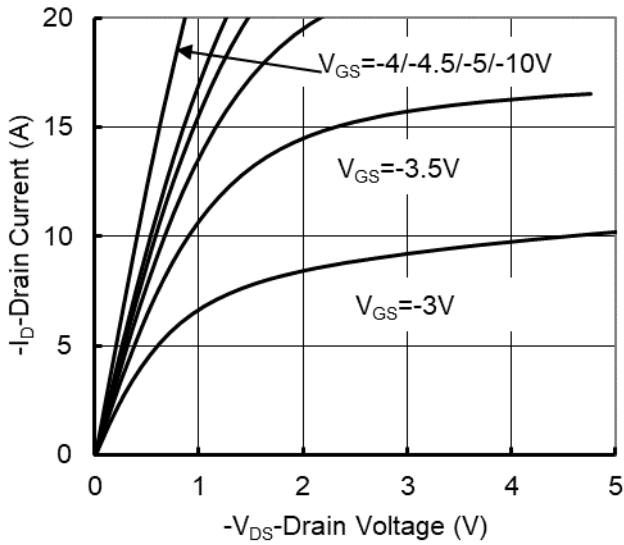


Figure1. Output Characteristics

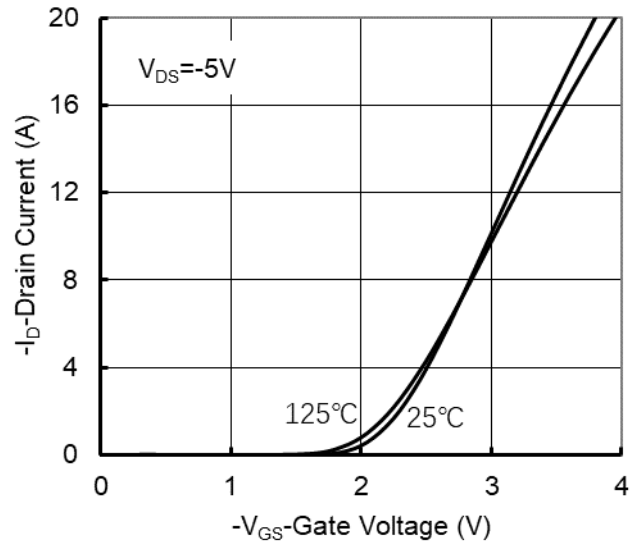


Figure2. Transfer Characteristics

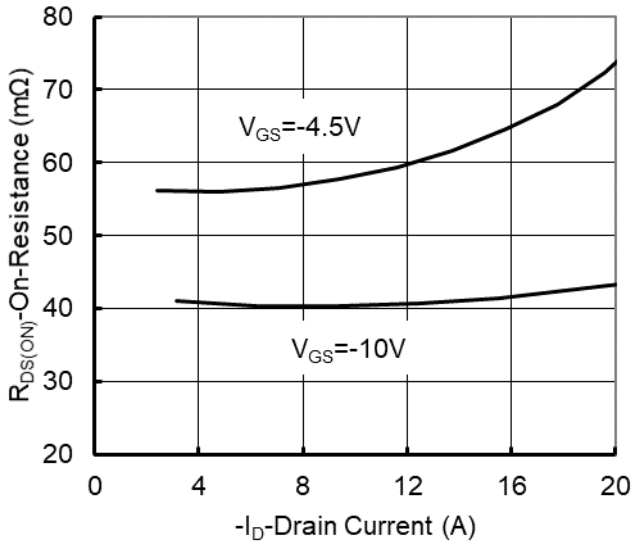


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

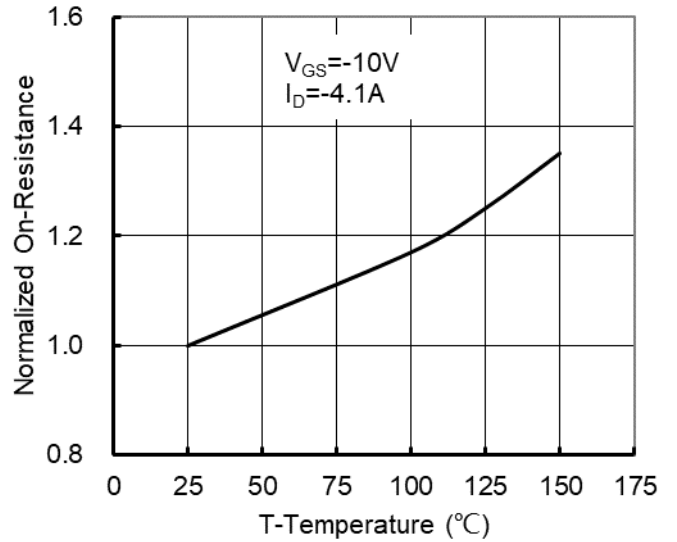


Figure 4: On-Resistance vs. Junction Temperature

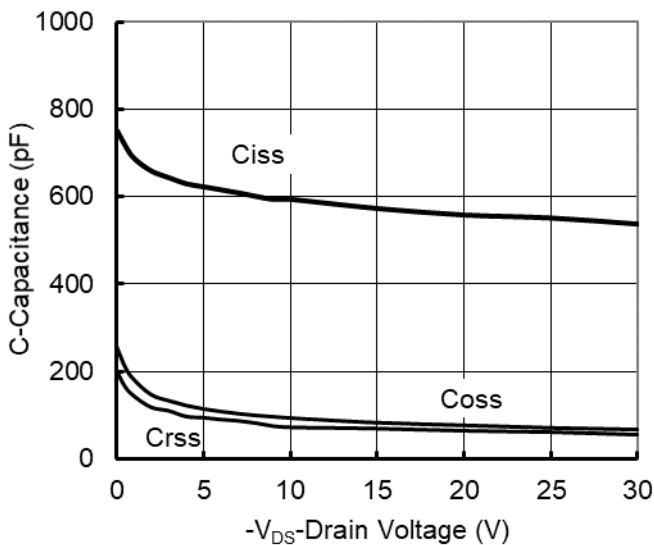


Figure5. Capacitance Characteristics

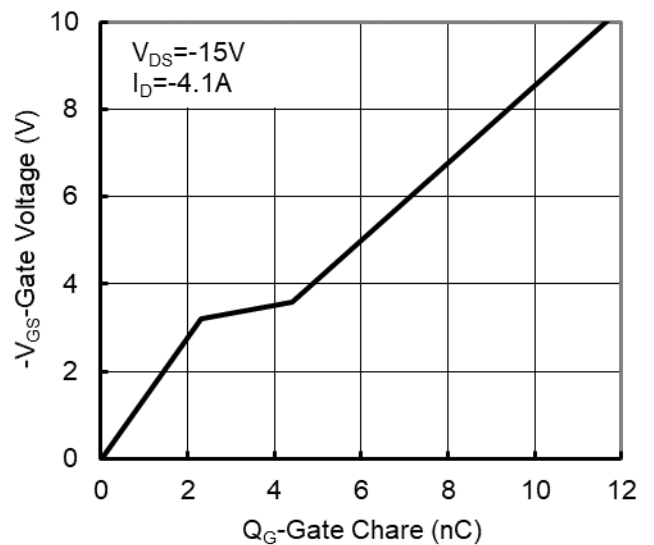


Figure6. Gate Charge

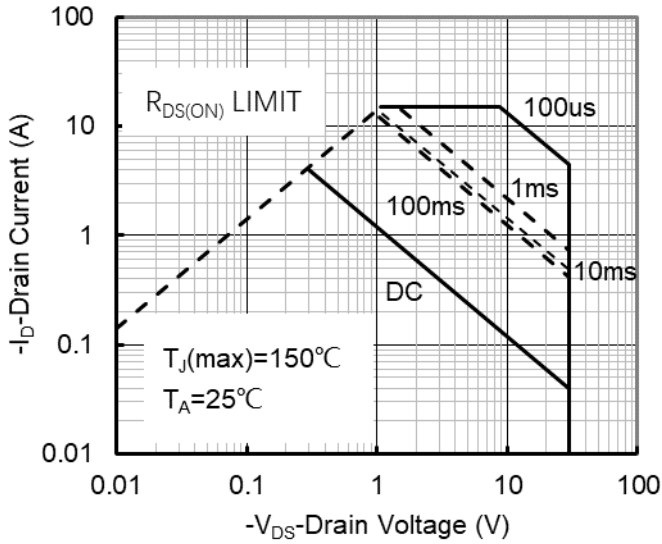


Figure7. Safe Operation Area

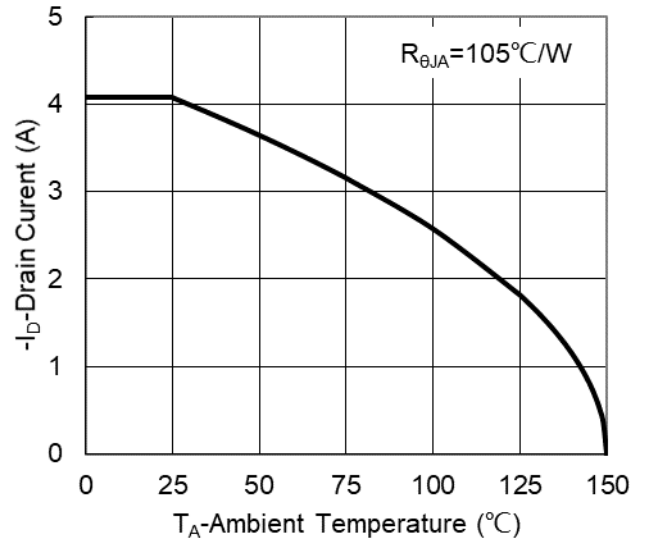


Figure8. Maximum Continuous Drain Current vs Ambient Temperature

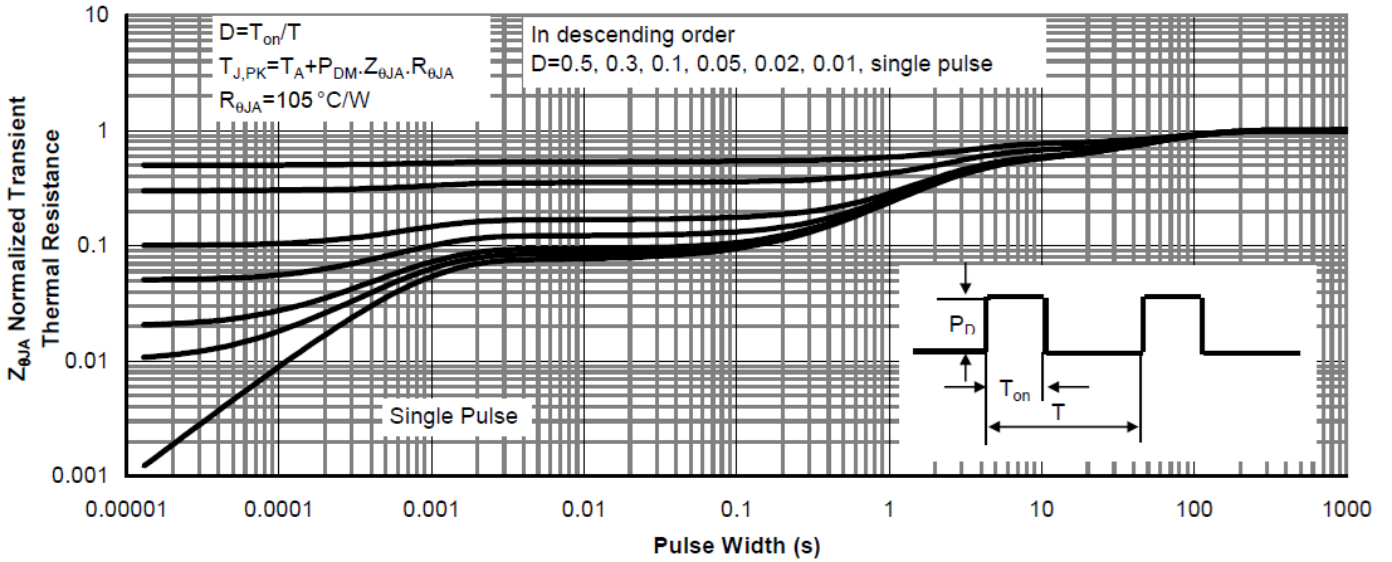
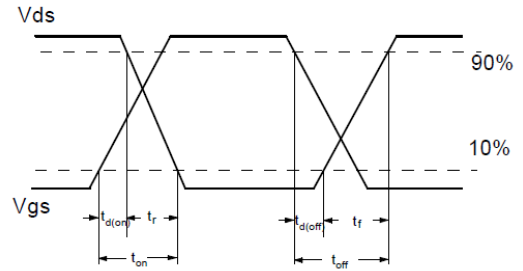
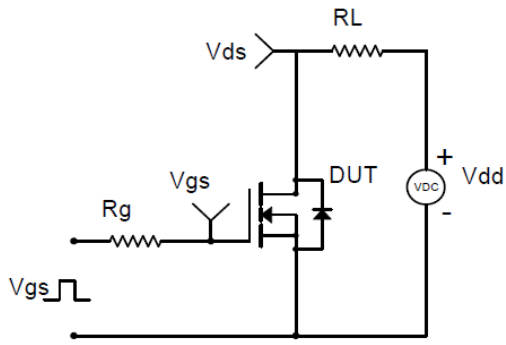
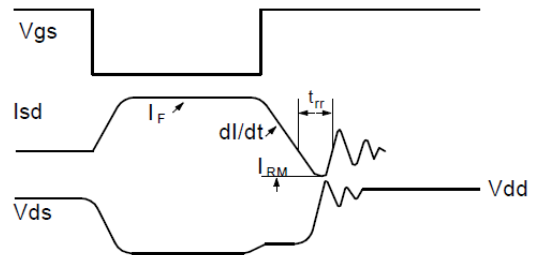
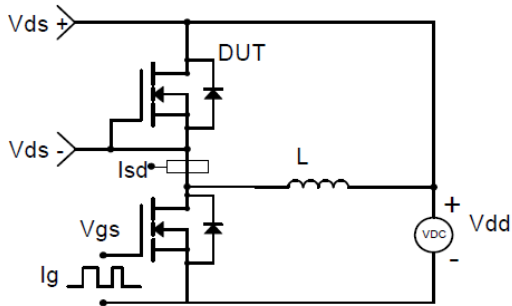


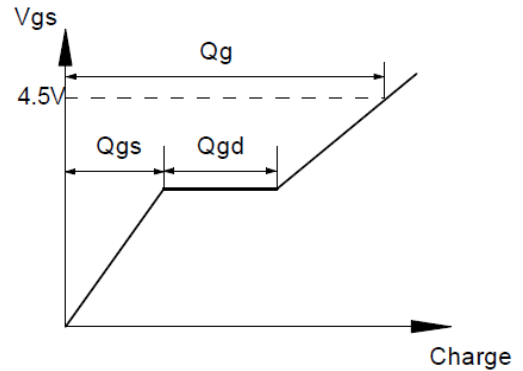
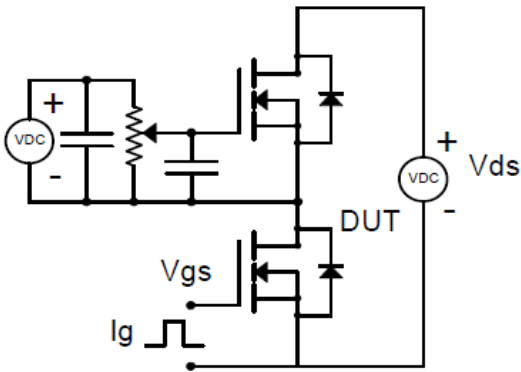
Figure9. Normalized Maximum Transient Thermal Impedance



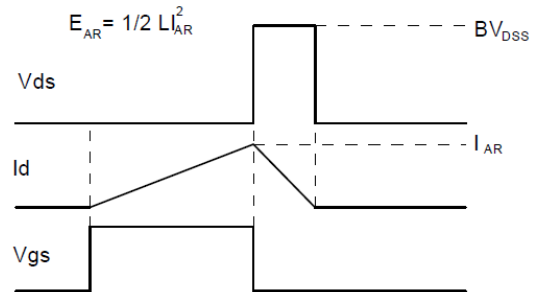
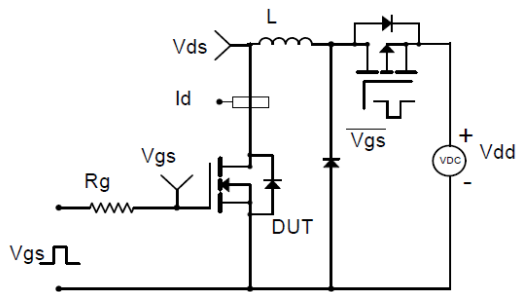
Resistive Switching Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Gate Charge Test Circuit & Waveform

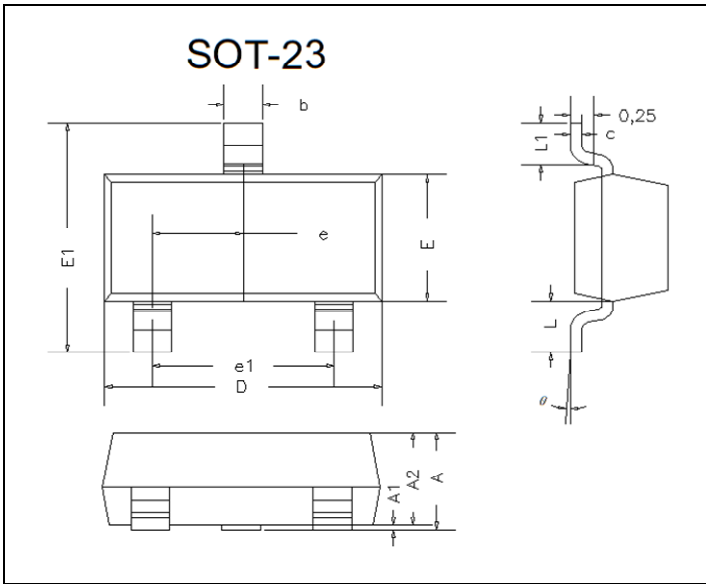


Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



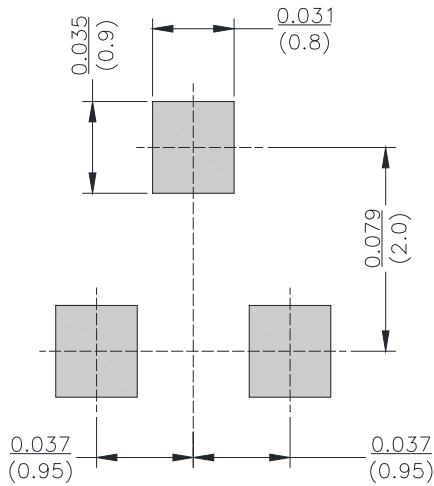
YJL3407AQ

■ SOT-23 Package information



DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.035	0.045	0.90	1.15	
A1	0.000	0.004	0.00	0.10	
A2	0.035	0.041	0.90	1.05	
b	0.012	0.020	0.30	0.50	
c	0.004	0.008	0.10	0.20	
D	0.110	0.118	2.80	3.00	
E	0.047	0.055	1.20	1.40	
E1	0.089	0.100	2.25	2.55	
e	0.370TYP		0.95TYP		
e1	0.071	0.079	1.80	2.00	
L	0.220REF		0.55REF		
L1	0.012	0.020	0.30	0.50	
θ	0°	8°	0°	8°	

■ SOT-23 Suggested Pad Layout





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